

Amendments to the Claims

40. (previously presented): A method of forming conductive lines comprising:

forming an oxide isolation grid between silicon structures;

forming conductive material within the oxide isolation grid to form a conductive grid therein; and

removing selected portions of the conductive material grid to define interconnect lines within the oxide isolation grid.

41. (previously presented): The method of forming conductive lines of claim 40, wherein forming an oxide isolation grid comprises forming individual oxide isolation regions over a silicon substrate by trench and refill technique.

42. (previously presented): The method of forming conductive lines of claim 40, wherein forming an oxide isolation grid comprises:

forming a plurality of silicon-containing islands over an insulative surface; and

forming oxide isolation regions between silicon-containing islands.

43. (previously presented): The method of forming conductive lines of claim 40, wherein forming conductive material within the oxide isolation grid comprises:

etching into the oxide isolation grid to define a network of outwardly-exposed trenches running within the oxide isolation grid;

forming conductive material within and over the outwardly-exposed trenches to a degree sufficient to completely fill the trenches; and planarizing the conductive material to isolate conductive material within the trenches and to define the conductive grid.